

PMN40LN

TrenchMOS™ logic level FET

Rev. 01 — 13 November 2002

Product data

1. Description

N-channel logic level field-effect power transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PMN40LN in SOT457 (TSOP6).

2. Features

- TrenchMOS™ technology
- Logic level compatible
- Surface mount package.

3. Applications

- Battery management
- High speed switch
- Low power DC to DC converter.

4. Pinning information

Table 1: Pinning - SOT457 (TSOP6), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,5,6	drain (d)	<p>Top view MBK092</p> <p>SOT457 (TSOP6)</p>	<p>MBB076</p>
3	gate (g)		
4	source (s)		

5. Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 10\text{ V}$	-	5.4	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$	-	1.75	W
T_j	junction temperature		-	150	°C
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 2.5\text{ A}; T_j = 25\text{ °C}$	32	38	mΩ
		$V_{GS} = 4.5\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ °C}$	40	45	mΩ

6. Limiting values

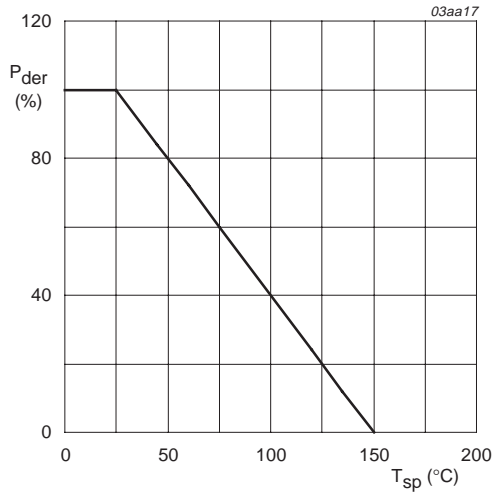
Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage (DC)		-	±15	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2 and 3	-	5.4	A
		$T_{sp} = 70\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2	-	4	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	21.6	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C};$ Figure 1	-	1.75	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C

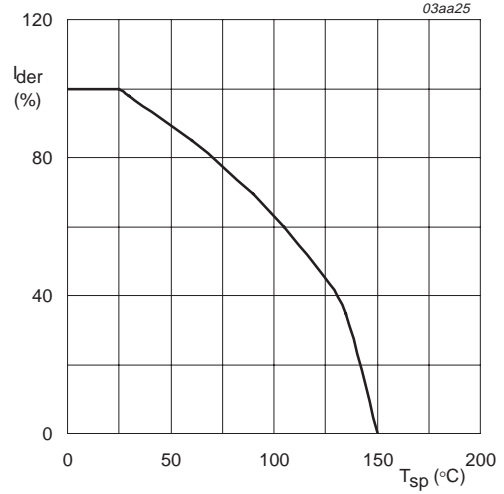
Source-drain diode

I_S	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	1.45	A
I_{SM}	peak source (diode forward) current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	5.8	A



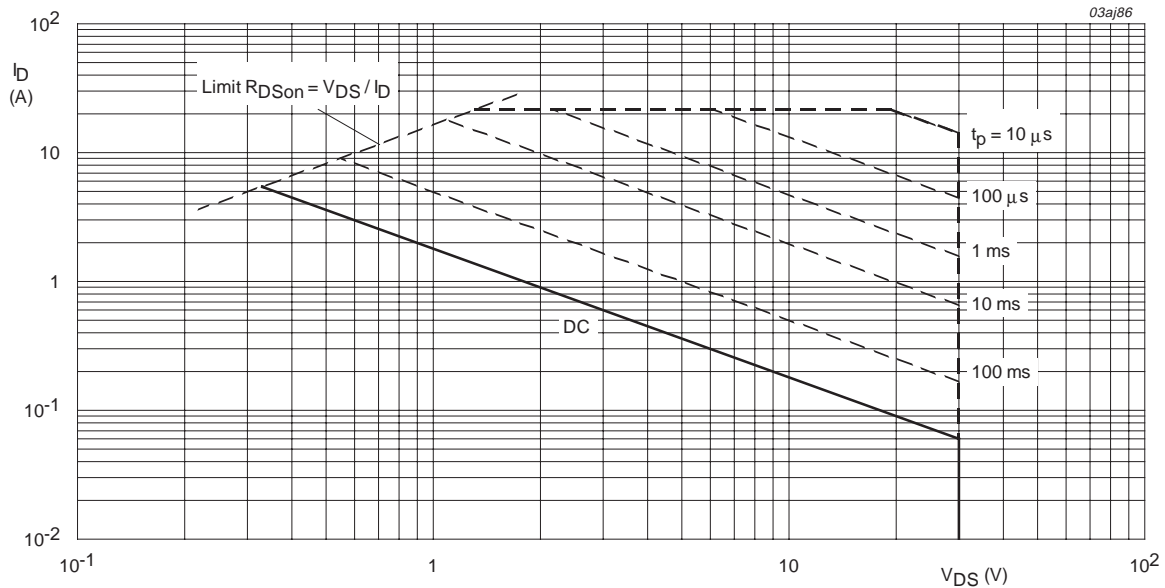
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



T_{sp} = 25 °C; V_{GS} = 10 V; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	mounted on a metal clad board; Figure 4	-	-	70	K/W

7.1 Transient thermal impedance

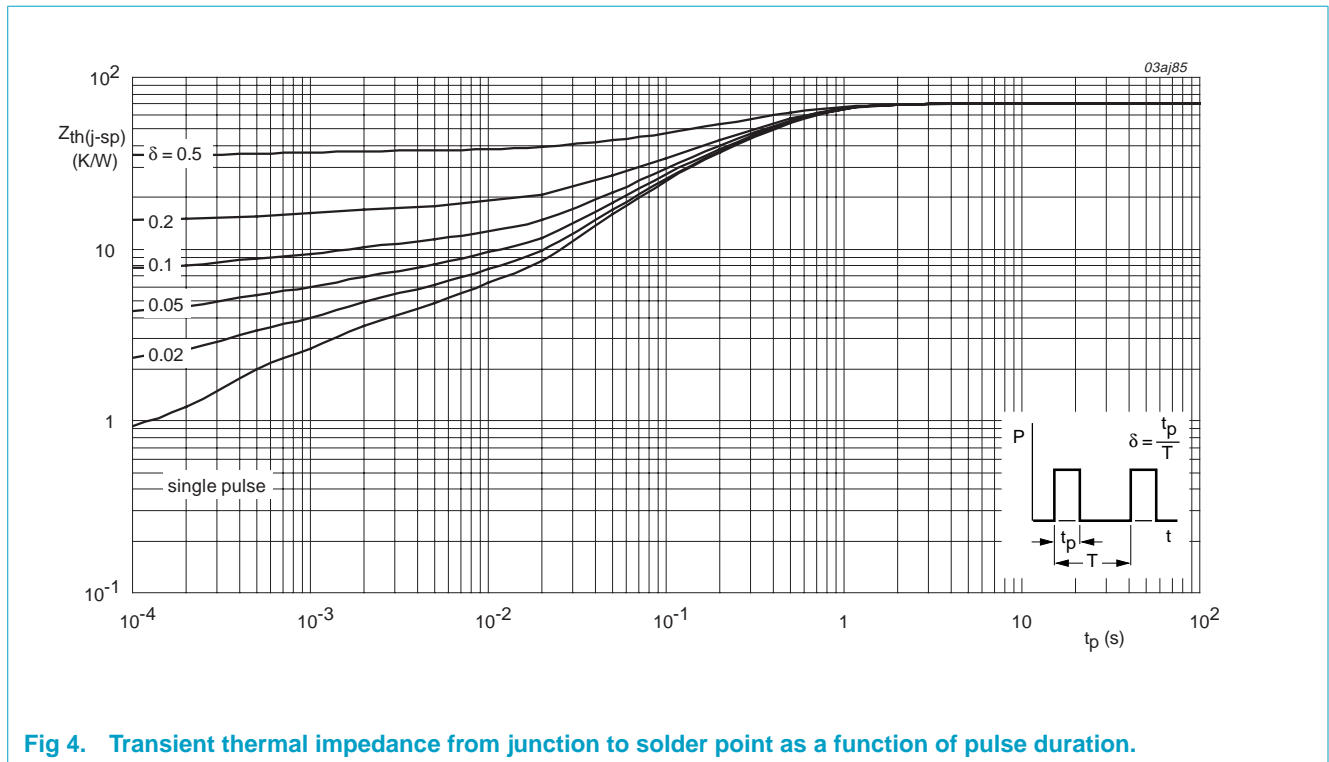
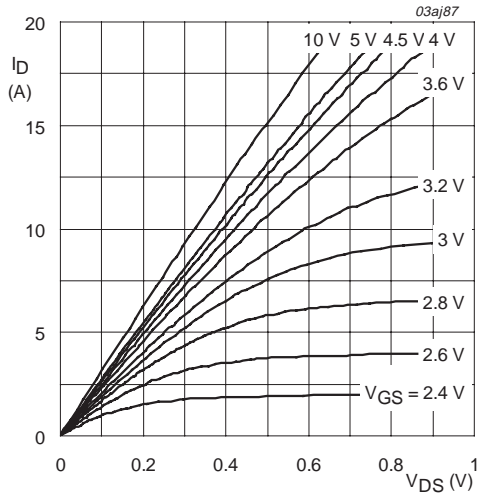


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration.

8. Characteristics

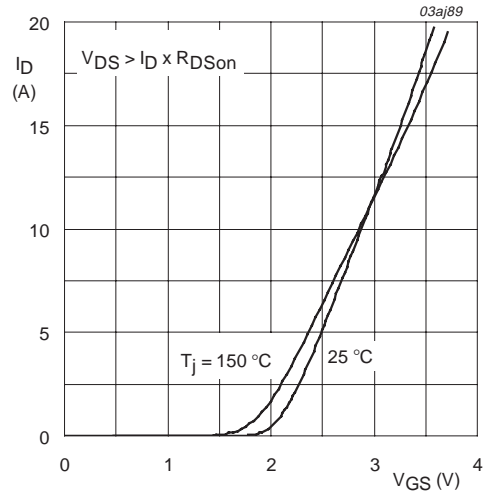
Table 5: Characteristics
 $T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	30	-	-	V
		$T_j = -55\text{ °C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$; Figure 9 $T_j = 25\text{ °C}$	1	1.5	2	V
		$T_j = 150\text{ °C}$	0.6	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.2	V
I_{DSS}	drain-source leakage current	$V_{DS} = 24\text{ V}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$	-	0.05	1	μA
		$T_j = 150\text{ °C}$	-	-	500	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 15\text{ V}$; $V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 2\text{ A}$; Figure 7 and 8 $T_j = 25\text{ °C}$	-	40	45	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	-	64	72	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}$; $I_D = 2.5\text{ A}$; Figure 7 $T_j = 25\text{ °C}$	-	32	38	$\text{m}\Omega$
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$I_D = 5\text{ A}$; $V_{DD} = 15\text{ V}$; $V_{GS} = 10\text{ V}$; Figure 13	-	13.8	-	nC
Q_{gs}	gate-source charge		-	1.8	-	nC
Q_{gd}	gate-drain (Miller) charge		-	2.4	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$; Figure 11	-	555	-	pF
C_{oss}	output capacitance		-	105	-	pF
C_{rss}	reverse transfer capacitance		-	70	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 15\text{ V}$; $R_L = 12\text{ }\Omega$;	-	5	-	ns
t_r	rise time	$V_{GS} = 10\text{ V}$; $R_G = 6\text{ }\Omega$	-	7	-	ns
$t_{d(off)}$	turn-off delay time		-	19	-	ns
t_f	fall time		-	8	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	$I_S = 1.7\text{ A}$; $V_{GS} = 0\text{ V}$; Figure 12	-	0.8	1.2	V



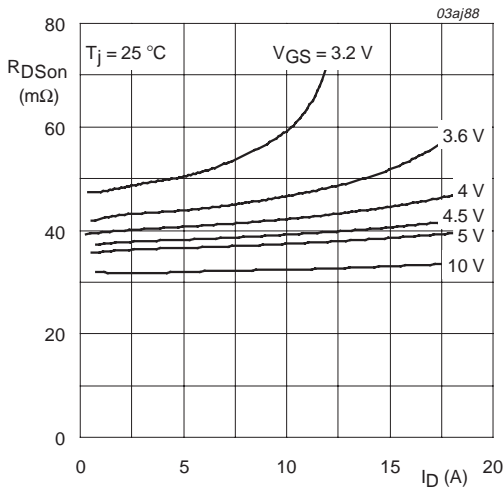
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



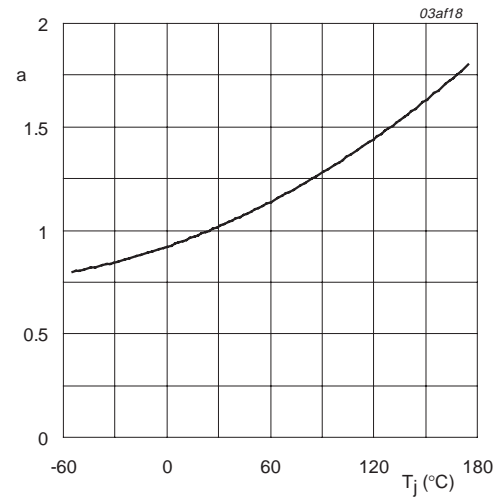
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



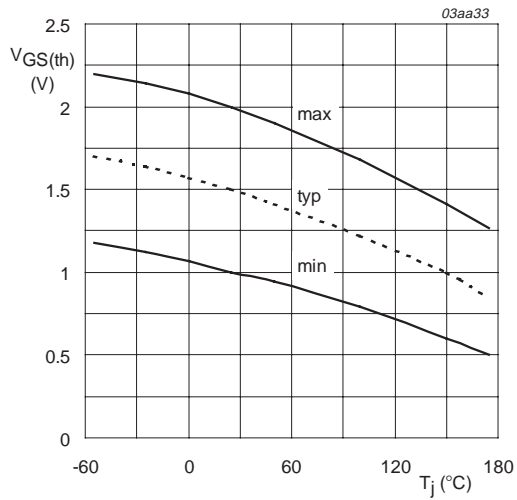
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



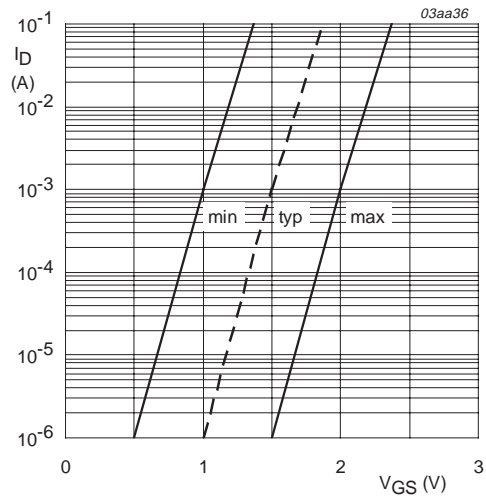
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



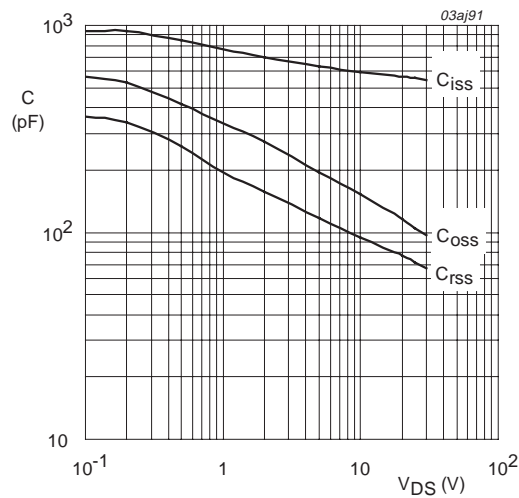
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



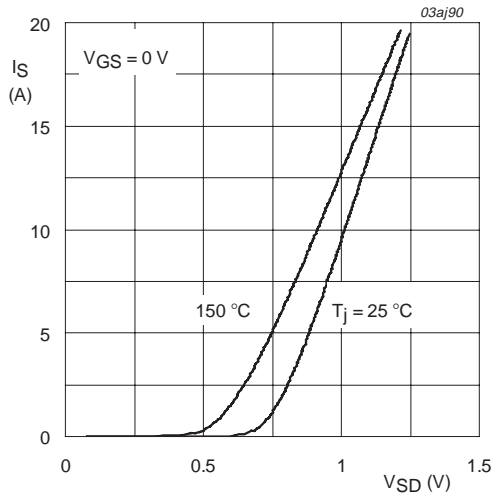
$T_j = 25 \text{ }^\circ\text{C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



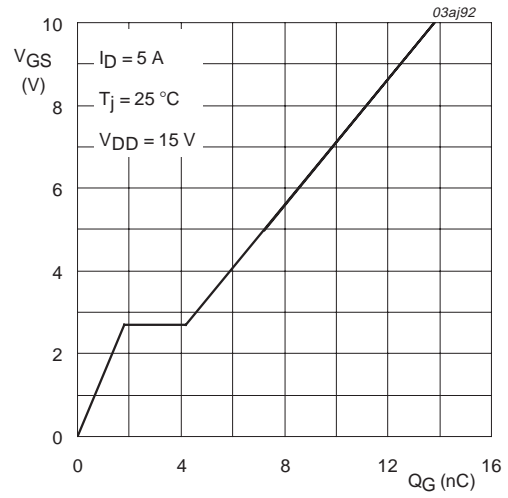
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25^\circ\text{C}$ and 150°C ; $V_{GS} = 0\text{ V}$

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 5\text{ A}$; $V_{DD} = 15\text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

9. Package outline

Plastic surface mounted package; 6 leads

SOT457

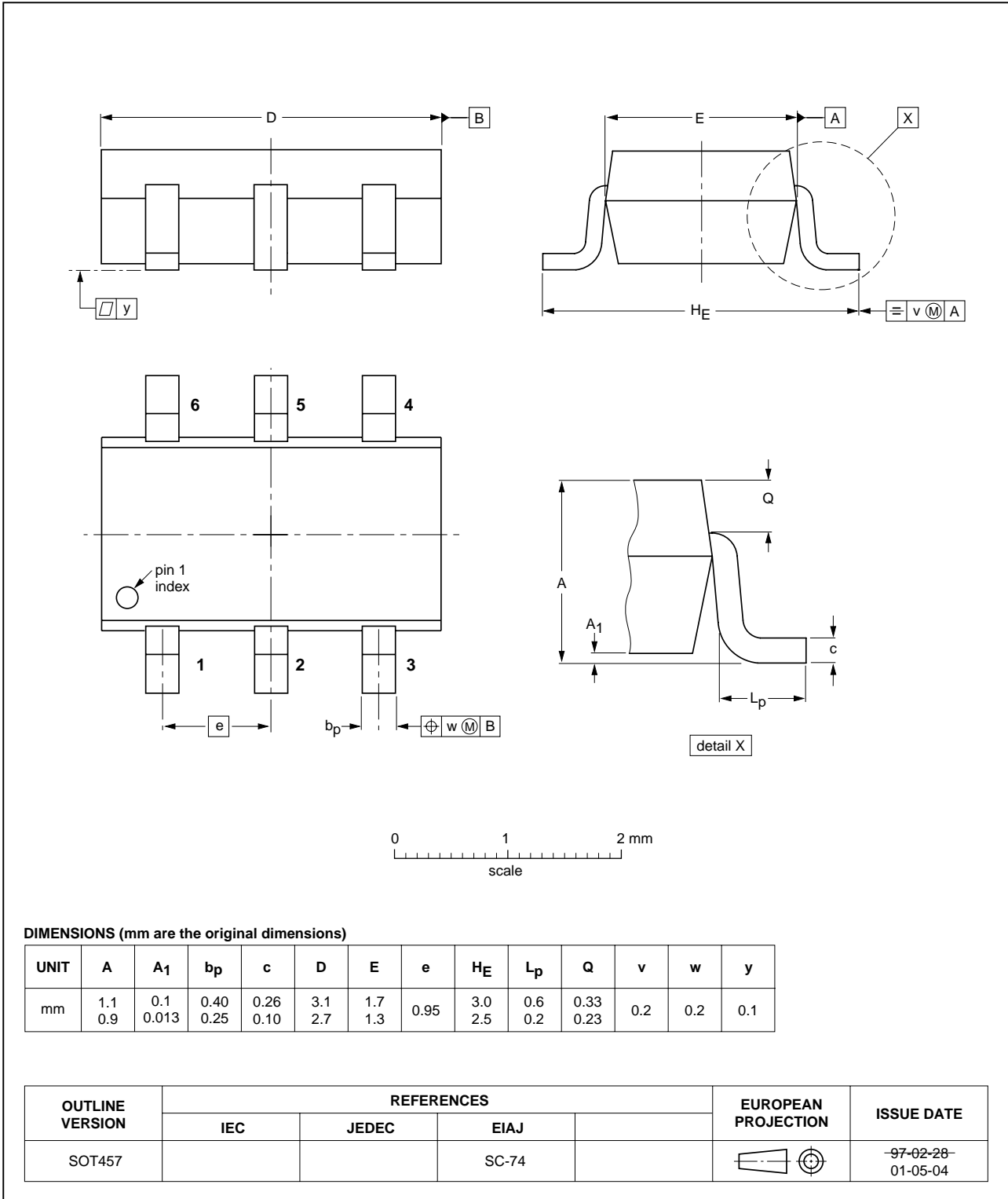


Fig 14. SOT457 (TSOP6).

10. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
01	20021113	-	Product data.

11. Trademarks

TrenchMOS — is a trademark of Koninklijke Philips Electronics N.V.

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Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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